IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently amended) A semiconductor device comprising:

a first insulating film comprising an organic material formed over a conductive layer;

a first metallic layer formed on said first insulating film;

a second metallic layer formed on said first metallic layer;

a second insulating film formed [on] in contact with said second metallic layer, said first metallic layer and said first insulating film; and

a pixel electrode formed on said second insulating film, said pixel electrode being connected to said second metallic layer at the bottom of a contact hole provided in said second insulating film,

wherein said conductive layer and said second metallic layer are directly connected to each other through a contact hole provided in said first metallic layer and said first insulating film.

2. (Original) The semiconductor device according to claim 1, wherein said first metallic layer is selected from the group consisting of aluminum and a material predominantly composed of aluminum.

3. (Original) The semiconductor device according to claim 1, wherein said second metallic layer is selected from the group consisting of titanium and a material predominantly composed of titanium.

4. (Original) The semiconductor device according to claim 1, wherein said organic material is an organic-based resin material predominantly selected from the group consisting of polyimide, polyimide-amide, polyamide, acrylics, and BCB (benzocyclobutane).

5. (Original) The semiconductor device according to claim 1, wherein said semiconductor device is selected form the group consisting of an active matrix liquid-crystal display device, an active matrix EL display device, and an active matrix EC display device.

6. (Original) The semiconductor device according to claim 1, wherein said semiconductor device is selected from the group consisting of a video camera, a digital camera, a projector, a goggle-type display device, a car navigation device, a personal computer, and a portable information terminal.

7. (Currently amended) A semiconductor device comprising:

a first insulating film comprising an organic material formed over a thin film transistor;

a first metallic layer formed on said first insulating film;

a second metallic layer formed on said first metallic layer;

a second insulating film formed [on] <u>in contact with</u> said second metallic layer, said first metallic layer and said first insulating film; and

a pixel electrode formed on said second insulating film, said pixel electrode being connected to said second metallic layer at the bottom of a contact hole provided in said second insulating film,

wherein a source region or a drain region of said thin film transistor and said second metallic layer are directly connected to each other through a contact hole provided in said first metallic layer and said first insulating film.

8. (Original) The semiconductor device according to claim 7, wherein said first metallic layer is selected from the group consisting of aluminum and a material predominantly composed of aluminum.

9. (Original) The semiconductor device according to claim 7, wherein said second metallic layer is selected from the group consisting of titanium and a material predominantly composed of titanium.

10. (Original) The semiconductor device according to claim 7, wherein said organic material is an organic-based resin material selected from the group consisting of polyimide, polyimide-amide, polyamide, acrylics, and BCB (benzocyclobutane).

11. (Original) The semiconductor device according to claim 7, wherein said semiconductor device is selected from the group consisting of an active matrix liquid-crystal display device, an active matrix EL display device, and an active matrix EC display device.

12. (Original) The semiconductor device according to claim 7, wherein said semiconductor device is selected from the group consisting of a video camera, a digital camera, a projector, a goggle-type display device, a car navigation device, a personal computer, and a portable information terminal.

13 – 18. (Canceled)

19. (Currently amended) A semiconductor device comprising:

a first insulating film comprising an organic material formed over a thin film transistor;

a first conductive layer formed on said first insulating film;

a second conductive layer formed on said first conductive layer;

a second insulating film formed [on] in contact with said second conductive layer, said first conductive layer and said first insulating film; and

a pixel electrode formed on said second insulating film, said pixel electrode being connected to said second conductive layer at the bottom of a contact hole provided in said second insulating film,

wherein a source region or a drain region and said second conductive layer are directly connected to each other through a contact hole provided in said first conductive layer and said first insulating film,

wherein said second conductive layer is contact with said first insulating film inside of said contact hole.

20. (Currently amended) The semiconductor device according to claim 19, wherein said first conductive layer is selected from the group consisting of aluminum and a material predominantly composed of aluminum.

21. (Currently amended) The semiconductor device according to claim 19, wherein said second conductive layer is selected from the group consisting of titanium and a material predominantly composed of titanium.

22. (Original) The semiconductor device according to claim 19, wherein said organic material is an organic-based resin material predominantly selected from the group consisting of polyimide, polyimide-amide, polyamide, acrylics, and BCB (benzocyclobutane).

23. (Original) The semiconductor device according to claim 19, wherein said semiconductor device is selected from the group consisting of an active matrix liquid-crystal display device, an active matrix EL display device, and an active matrix EC display device.

24. (Original) The semiconductor device according to claim 19, wherein said semiconductor device is selected from the group consisting of a video camera, a digital camera, a projector, a goggle-type display device, a car navigation device, a personal computer, and a portable terminal.

25 - 27. (Canceled)

28. (Currently amended) A semiconductor device comprising:

a thin film transistor formed over a substrate, said thin film transistor having a semiconductor layer and a gate electrode adjacent to said semiconductor layer with a gate insulating film interposed therebetween;

a first insulating film formed over said thin film transistor;

a first conductive layer formed on said first insulating film;

a second conductive layer formed on said first conductive layer;

a second insulating film formed [on] in contact with said second conductive layer, said first conductive layer and said first insulating film; and

a pixel electrode formed on said second insulating film, said pixel electrode being connected to said second conductive layer at the bottom of a contact hole provided in said second insulating film,

wherein said second conductive layer is directly connected to said semiconductor layer through a contact hole provided in said first conductive layer and said first insulating film.

29. (Previously presented) The semiconductor device according to claim 28, wherein said first conductive layer is selected from the group consisting of aluminum and a material predominantly composed of aluminum.

30. (Previously presented) The semiconductor device according to claim 28, wherein said second conductive layer is selected from the group consisting of titanium and a material predominantly composed of titanium.

31. (Previously presented) The semiconductor device according to claim 28, wherein said organic material is an organic-based resin material predominantly selected from the group consisting of polyimide, polyimide-amide, polyamide, acrylics, and BCB (benzocyclobutane).

32. (Previously presented) The semiconductor device according to claim 28, wherein said semiconductor device is selected from the group consisting of an active matrix liquid-crystal display device, an active matrix EL display device, and an active matrix EC display device.

33. (Previously presented) The semiconductor device according to claim 28, wherein said semiconductor device is selected from the group consisting of a video camera, a digital camera, a projector, a goggle-type display device, a car navigation device, a personal computer, and a portable information terminal.

34. (Currently amended) A semiconductor device comprising:

a thin film transistor formed over a substrate, said thin film transistor having a semiconductor layer and a gate electrode adjacent to said semiconductor layer with a gate insulating film interposed therebetween;

a first insulating film comprising an organic material formed over said thin film transistor;

a first conductive layer formed on said first insulating film;

a second conductive layer formed on said first conductive layer;

a second insulating film formed [on] <u>in contact with</u> said second conductive layer, said first conductive layer and said first insulating film; and

a pixel electrode formed on said second insulating film, said pixel electrode being connected to said second conductive layer at the bottom of a contact hole provided in said second insulating film,

wherein said second conductive layer is directly connected to said semiconductor layer through a contact hole provided in said first conductive layer and said first insulating film.

35. (Previously presented) The semiconductor device according to claim 34, wherein said first conductive layer is selected from the group consisting of aluminum and a material predominantly composed of aluminum.

36. (Previously presented) The semiconductor device according to claim 34, wherein said second conductive layer is selected from the group consisting of titanium and a material predominantly composed of titanium.

37. (Previously presented) The semiconductor device according to claim 34, wherein said organic material is an organic-based resin material predominantly selected from the group consisting of polyimide, polyimide-amide, polyamide, acrylics, and BCB (benzocyclobutane).

38. (Previously presented) The semiconductor device according to claim 34, wherein said semiconductor device is selected from the group consisting of an active matrix liquid-crystal display device, an active matrix EL display device, and an active matrix EC display device.

39. (Previously presented) The semiconductor device according to claim 34, wherein said semiconductor device is selected from the group consisting of a video camera, a digital camera, a projector, a goggle-type display device, a car navigation device, a personal computer, and a portable information terminal.

40. (Currently amended) A semiconductor device comprising:

a thin film transistor formed over a substrate, said thin film transistor having a semiconductor layer and a gate electrode adjacent to said semiconductor layer with a gate insulating film interposed therebetween;

a first insulating film formed over said thin film transistor;

a first wiring formed on said first insulating film;

a second wiring formed on said first wiring;

a second insulating film formed [on] <u>in contact with</u> said second wiring, said first wiring and said first insulating film; and

a pixel electrode formed on said second insulating film, said pixel electrode being connected to said second wiring at the bottom of a contact hole provided in said second insulating film,

wherein said second wiring is directly connected to said semiconductor layer through a contact hole provided in said first wiring and said first insulating film.

41. (Previously presented) The semiconductor device according to claim 40, wherein said first wiring is selected from the group consisting of aluminum and a material predominantly composed of aluminum.

42. (Previously presented) The semiconductor device according to claim 40, wherein said second wiring is selected from the group consisting of titanium and a material predominantly composed of titanium.

43. (Previously presented) The semiconductor device according to claim 40, wherein said first insulating layer comprises an organic-based resin material predominantly selected from the group consisting of polyimide, polyimide-amide, polyamide, acrylics, and BCB (benzocyclobutane).

44. (Previously presented) The semiconductor device according to claim 40, wherein said semiconductor device is selected from the group consisting of an active matrix liquid-crystal display device, an active matrix EL display device, and an active matrix EC display device.

45. (Previously presented) The semiconductor device according to claim 40, wherein said semiconductor device is selected from the group consisting of a video camera, a digital camera, a projector, a goggle-type display deice, a car navigation device, a personal computer, and a portable information terminal.